

Specification

Products

Type

RXT2907A

1. SCOPE

RXT2907A

1.1 Scope.

This specification covers the detail requirements for one type PNP silicon epitaxial planar transistor designed for audio frequency small signal amplifier.

1.2 Physical dimensions.

See figure 1.

1.3 Absolute maximum ratings.

(Ta=25 °C)

Collector to base voltage

V_{CBO}

.....

-60V

Collector to emitter voltage

V_{CEO}

.....

-60V

Emitter to base voltage

V_{EBO}

.....

-5V

Collector current

I_C

.....

-600mA

Power dissipation

P_C

.....

500mW

Junction temperature

T_j

.....

150°C

Storage temperature range

T_{stg}

.....

-55~150°C

2. Electrical characteristics

(Ta=25 °C)

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
BVCBO	$I_C=-10\mu A$	-60	-	-	V
BVCEO	$I_C=-10mA$	-60	-	-	V
BVEBO	$I_E=-10\mu A$	-5	-	-	V
ICBO	$V_{CB}=-50V$	-	-	-100	nA
ICES	$V_{CE}=-30V$	-	-	-100	nA
IEBO	$V_{EB}=-3V$	-	-	-100	nA
VCE(sat) 1	$I_C=-150mA, I_B=-15mA$	-	-	-0.4	V
VCE(sat) 2	$I_C=-500mA, I_B=-50mA$	-	-	-1.6	V
VBE(sat) 1	$I_C=-150mA, I_B=-15mA$	-	-	-1.3	V
VBE(sat) 2	$I_C=-500mA, I_B=-50mA$	-	-	-2.6	V
hFE 1	$V_{CE}=-10V, I_C=-0.1mA$	75	-	-	
hFE 2	$V_{CE}=-10V, I_C=-1mA$	100	-	-	
hFE 3	$V_{CE}=-10V, I_C=-10mA$	100	-	-	
hFE 4	$V_{CE}=-10V, I_C=-150mA$	100	-	300	
hFE 5	$V_{CE}=-10V, I_C=-500mA$	50	-	-	
fT	$V_{CE}=-20V, I_C=-50mA, f=100MHz$	200	-	-	MHz
Cob	$V_{CB}=-10V, f=100KHz$	-	-	8	pF
Cib	$V_{EB}=-2V, f=100KHz$	-	-	30	pF

ROHM CO., LTD.

Design

H. Nakano

Approval

S. Suma

Specification No.

TLRXT2907A-1

Date

9/24/86

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		RXT2907A

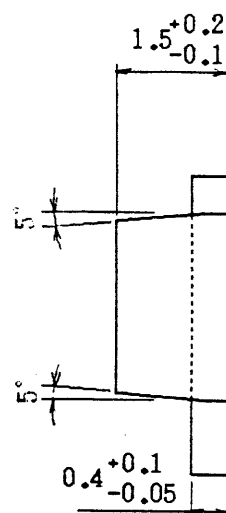
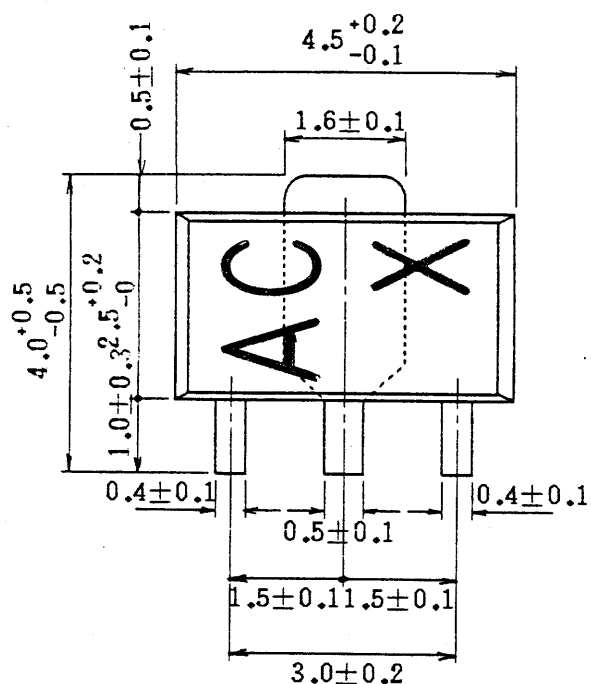
PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
t on		—	—	50	n S
t d	VCC=-30V, VBE(OFF)=-1.5V	—	—	10	n S
t r	I C=-150mA, I B1=-15mA	—	—	40	n S
t off		—	—	100	n S
t s	VCC=-30V, I C=-150mA	—	—	80	n S
t f	I B1= I B2=-15mA	—	—	30	n S

Specification

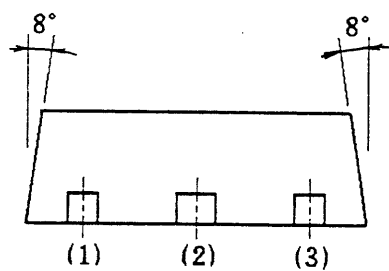
Products

Type

RXT2907A



UNIT: mm



- (1) Base
- (2) Collector
- (3) Emitter

AC
Marking code

X
Lot.No